



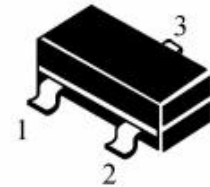
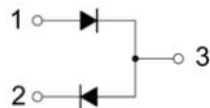
安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

MMBD7000

Switching Diode 开关二极管

■ SOT-23 Internal Configuration 内部结构



■ Features 特点

Characteristic 特性参数	Symbol 符号	Max 最大值	Unit 单位
Power dissipation 耗散功率	$P_D(T_a=25^\circ\text{C})$	225	mW
Forward Current 正向电流	I_F	200	mA
Reverse Voltage 反向电压	V_R	100	V
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ\text{C}$	

■ Device Marking 产品打标

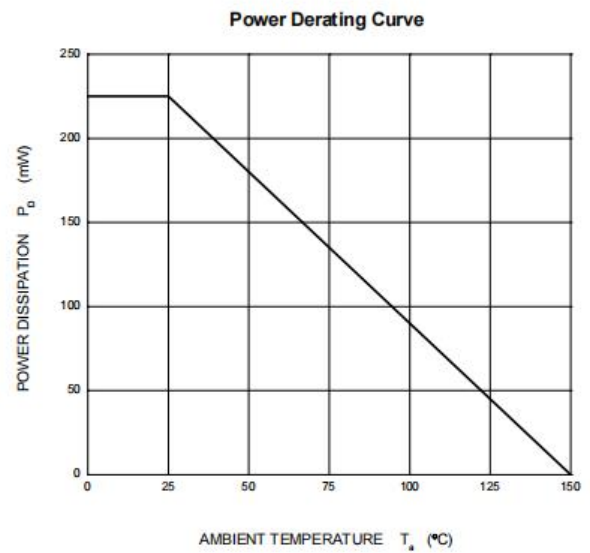
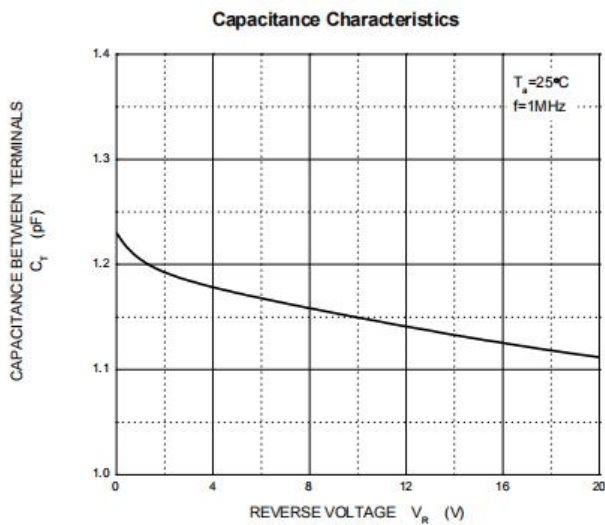
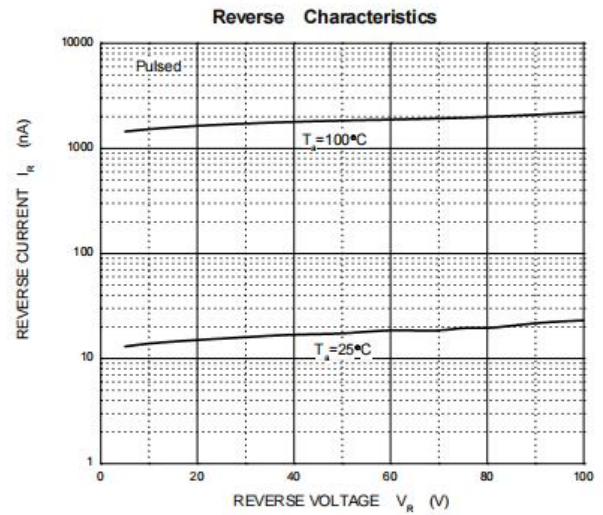
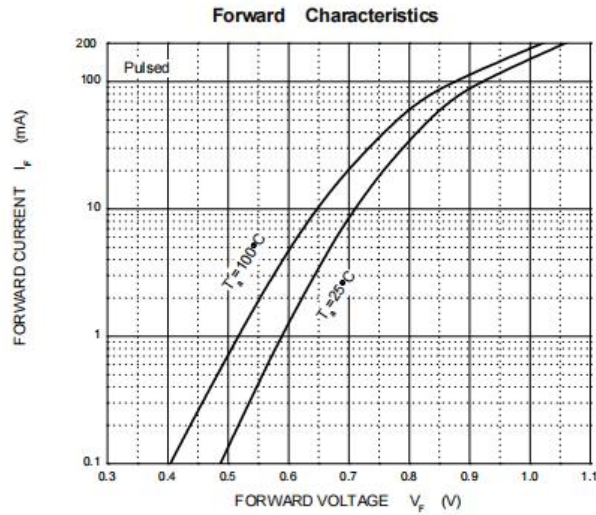
MMBD7000=M5C

■ Electrical Characteristics 电特性

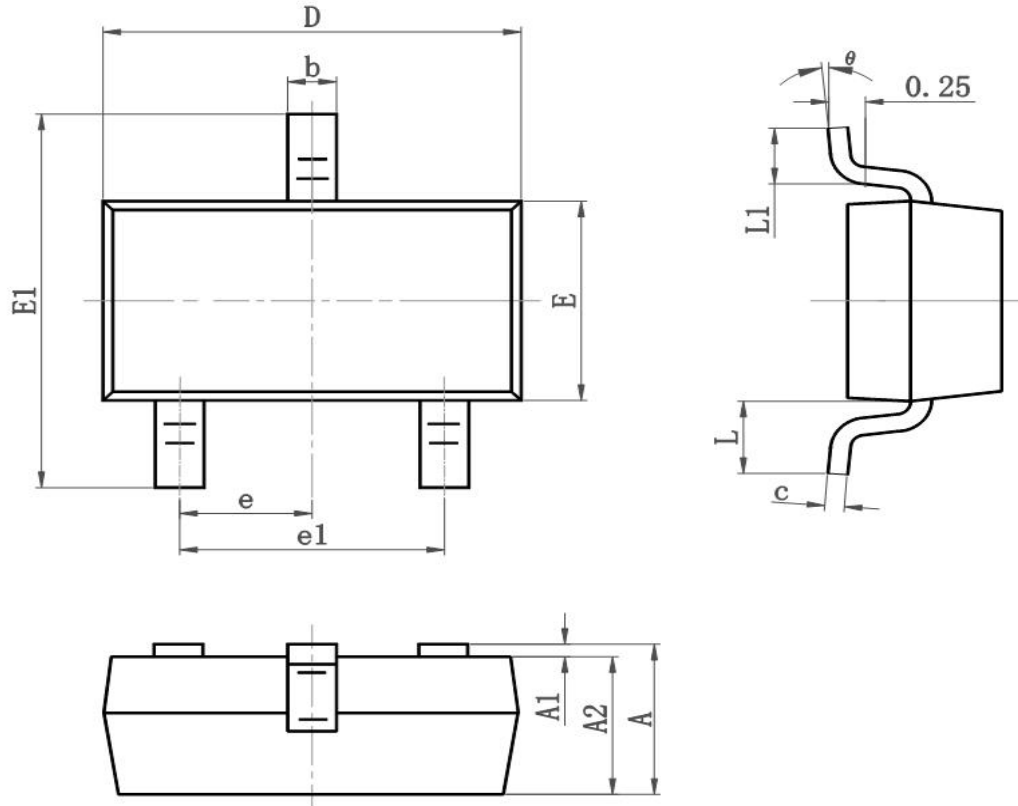
($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压 ($I_R=100\mu\text{A}$)	$V_{(BR)}$	100	—	V
Reverse Leakage Current 反向漏电流 ($V_R=50\text{V}$) ($V_R=100\text{V}$)	I_R	—	1 3	μA μA
Forward Voltage 正向电压 ($I_F=1\text{mA}$) ($I_F=10\text{mA}$) ($I_F=100\text{mA}$)	V_F	0.55 0.67 0.75	0.7 0.82 1.1	V
Diode Capacitance 二极管电容 ($V_R=0\text{V}$, $f=1\text{MHz}$)	C_D	—	2	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	4	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°